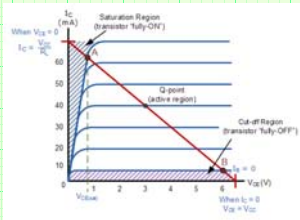


Solid State Devices

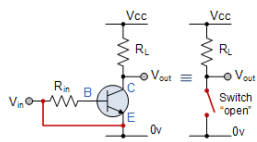
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 TECH 3821 – Industrial Electronics
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Transistors as a Switch

- In TECH 2821 (Solid State Technology) you used transistors (NPN/PNP) in the "Active" region as an amplifying device.
- But transistors can also be used as a switch (ie the "Saturation" and "Cut-off" Regions)



Cut-off



- The input and Base are grounded (0v)
- Base-Emitter voltage $V_{BE} < 0.7v$
- Base-Emitter junction is reverse biased
- Base-Collector junction is reverse biased
- Transistor is "fully-OFF" (Cut-off region)
- No Collector current flows ($I_C = 0$)
- $V_{OUT} = V_{CE} = V_{CC} = "1"$
- Transistor operates as an "open switch"

NPN Transistor Relay Driver	
	<ul style="list-style-type: none"> In order for the Base current to flow, the Base input terminal must be made more positive than the Emitter by increasing it above the 0.7 volts needed for a silicon device. By varying this Base-Emitter voltage VBE, the Base current is also altered and which in turn controls the amount of Collector current flowing through the transistor as previously discussed.

NPN Transistor Relay Driver	
	<ul style="list-style-type: none"> When maximum Collector current flows the transistor is said to be Saturated. The value of the Base resistor determines how much input voltage is required and corresponding Base current to switch the transistor fully "ON".

Calculations	
<ul style="list-style-type: none"> A simple configuration for an NPN transistor switch circuit. <ul style="list-style-type: none"> R_L (load) - lamp or relay or some other device that needs a larger current than the input is able to drive directly. R_b (Base Resistor) - used to prevent damage at the base of the transistor. This needs to be large enough to prevent damage to the transistor, but should still allow sufficient current to ensure the transistor switches on. 	

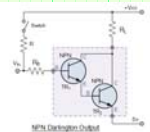
Calculations (cont)	
○	<p>• First we calculate the appropriate load current:</p> $I_c = \frac{V_{cc} - V_{ce}}{R_L}$ <p>• Where</p> <ul style="list-style-type: none"> - I_c - Collector current - V_{cc} - supply voltage - V_{ce} - voltage drop across the transistor (Collector to Emitter) from the data sheet - R_L - load resistance <p>○ Check the datasheet to ensure the transistor can handle the current required for the load!</p>

Calculations (cont)	
○	<p>• Calculate the minimum base current</p> $I_b = \frac{I_c}{\beta}$ <p>Where</p> <ul style="list-style-type: none"> • β or h_{FE} - gain • I_b - base current • I_c - Collector current <p>○</p>

Calculations (cont)	
○	<p>• Calculate R_b</p> $R_b = \frac{V_{in} - V_{be}}{I_b * 10}$ <p>• Where:</p> <ul style="list-style-type: none"> - R_b - Base resistor - V_{in} - voltage in (at base) - V_{be} - voltage drop Base to Emitter (from data sheet) - I_b - Base Current (from previous calculation) - 10 - Fudge factor <p>○ As a rule of thumb, we use a fudge factor of 10 to ensure we go into full saturation (If $I_b * 10$ exceeds the maximum base current then a value below the maximum base current should be used)</p>

Example #1	
○	<ul style="list-style-type: none"> Given <ul style="list-style-type: none"> $\beta = 200$ $I_c = 4mA$ $I_b = 20\mu A$ $V_{be} = 0.7V$ Find the value of the Base resistor (R_b) required to switch the load fully "ON" when the input terminal voltage exceeds 2.5v. $R_b = \frac{V_{in} - V_{be}}{I_b \times 10} = \frac{2.5V - 0.7V}{20\mu A \times 10} = 9K$ (note, the biggest resistor you can use is 90K (taking out the 10x fudge factor)
○	

Example #2	
○	<ul style="list-style-type: none"> Given <ul style="list-style-type: none"> $\beta = 200$ $I_c = 200mA$ $V_{be} = 0.7V$ $V_{in} = 5V$ $I_b = \frac{I_c}{\beta} = \frac{200mA}{200} = 1mA$ $R_b = \frac{V_{in} - V_{be}}{I_b \times 10} = \frac{5.0V - 0.7V}{1mA \times 10} = 43K$
○	

Darlington Pair	
○	<ul style="list-style-type: none"> Sometimes the DC current gain of the bipolar transistor is too low to directly switch the load current or voltage. In these cases multiple switching transistors are used. <ul style="list-style-type: none"> one small input transistor is used to switch "ON" or "OFF" a much larger current handling output transistor. To maximise the signal gain, the two transistors are connected in a "Darlington Pair" configuration where the amplification factor is the product of the two individual transistors. <div style="border: 1px solid black; padding: 5px; display: inline-block; margin: 10px;"> $\beta_{TOTAL} = \beta_1 \times \beta_2$ </div> 
○	

Back EMF Diode	
○	<ul style="list-style-type: none"> Flyback Diodes are common when using transistor circuits to turn on/off inductive devices (motors, relays, etc). They are also called: <ul style="list-style-type: none"> - Snubber Diodes - Back EMF Diodes - Flyback Diodes - Flywheel Diode
○	<p>The diagram shows a circuit where a transistor is used to switch an inductive load. The base of the transistor is driven by a base resistor R_B connected to a base current source I_B. The collector is connected to a collector resistor R_C and the inductive load. The emitter is grounded. A flyback diode is connected in parallel with the inductive load, with its cathode to the collector and its anode to ground. The collector-emitter voltage is labeled V_{CE} and the load current is I_L. The diode is labeled 'Flywheel Diode'.</p>

Summary	
○	<ul style="list-style-type: none"> Transistor switches can be used to switch and control lamps, relays or even motors. When using the bipolar transistor as a switch they must be either "fully-OFF" or "fully-ON". Transistors that are fully "ON" are said to be in their Saturation region. Transistors that are fully "OFF" are said to be in their Cut-off region. When using the transistor as a switch, a small Base current controls a much larger Collector load current.
○	<ul style="list-style-type: none"> When using transistors to switch inductive loads such as relays and solenoids, a "Flywheel Diode" is used.
